

Thyristor Module

$$V_{RRM} = 800V$$

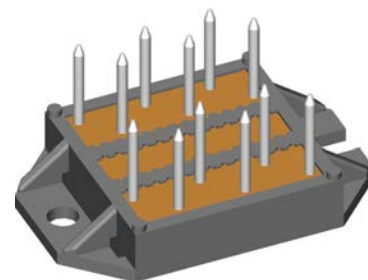
$$I_{TAV} = 16A$$

$$V_T = 1,19V$$

AC Controlling
 3~ full-controlled

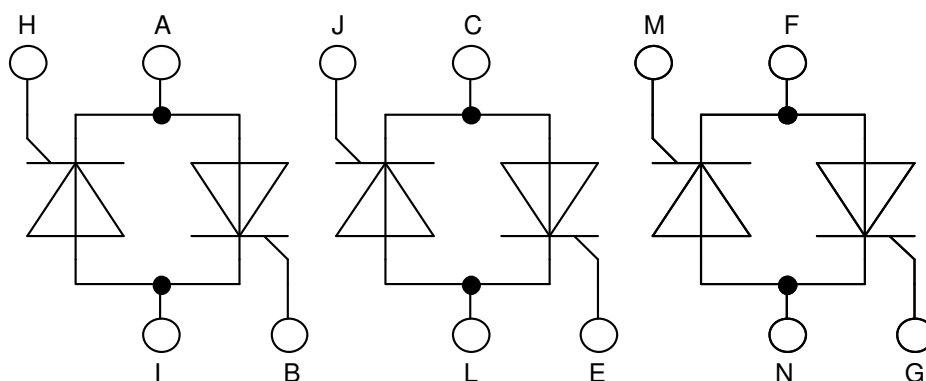
Part number

VWO35-08HO7



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: ECO-PAC1

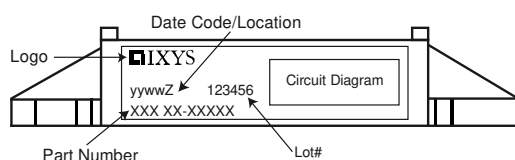
- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				800	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			50	μA
		$V_{R/D} = 800\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			2	mA
V_T	forward voltage drop	$I_T = 15\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,23	V
		$I_T = 30\text{ A}$				1,48	V
		$I_T = 15\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,19	V
		$I_T = 30\text{ A}$				1,51	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 125^{\circ}\text{C}$			16	A
I_{RMS}	RMS forward current per phase	180° sine				35	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}\text{C}$			0,88	V
r_T	slope resistance					21	m Ω
R_{thJC}	thermal resistance junction to case					1,3	K/W
R_{thCH}	thermal resistance case to heatsink				0,5		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			77	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			200	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			215	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			170	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			185	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			200	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			190	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			145	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			140	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		7		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 125^{\circ}\text{C}$			5	W
		$t_p = 300\text{ }\mu\text{s}$				2,5	W
P_{GAV}	average gate power dissipation					0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 45\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0,15\text{ A}/\mu\text{s};$ $I_G = 0,15\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 15\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}\text{C}$			500	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1,5	V
			$T_{VJ} = -40^{\circ}\text{C}$			2,5	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			25	mA
			$T_{VJ} = -40^{\circ}\text{C}$			50	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			0,2	V
I_{GD}	gate non-trigger current					3	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			75	mA
		$I_G = 0,1\text{ A}; di_G/dt = 0,1\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			50	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0,1\text{ A}; di_G/dt = 0,1\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 15\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$		150		μs

Package ECO-PAC1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	<i>RMS current</i>	per terminal			40	A
T_{VJ}	<i>virtual junction temperature</i>		-40		125	°C
T_{op}	<i>operation temperature</i>		-40		100	°C
T_{stg}	<i>storage temperature</i>		-40		125	°C
Weight				19		g
M_D	<i>mounting torque</i>		1,4		2	Nm
$d_{Spp/App}$	<i>creepage distance on surface striking distance through air</i>	<i>terminal to terminal</i>	6,0			mm
$d_{Spb/Apb}$		<i>terminal to backside</i>	10,0			mm
V_{ISOL}	<i>isolation voltage</i>	t = 1 second	3600			V
		t = 1 minute	3000			V

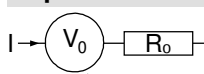


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VWO35-08ho7	VWO35-08ho7	Box	25	491837

Equivalent Circuits for Simulation

* on die level

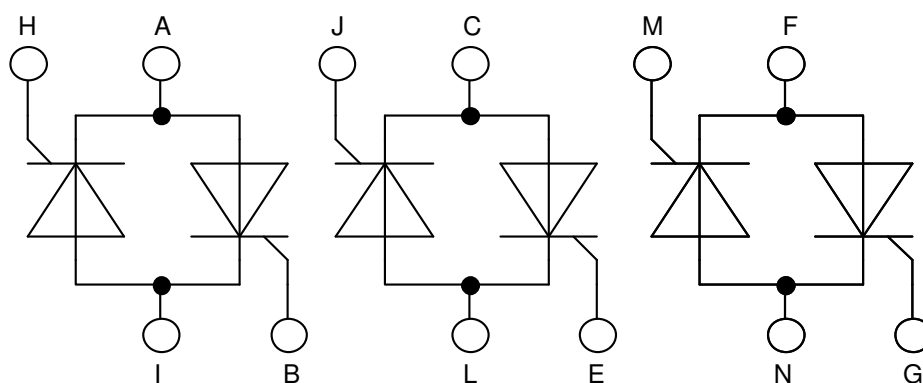
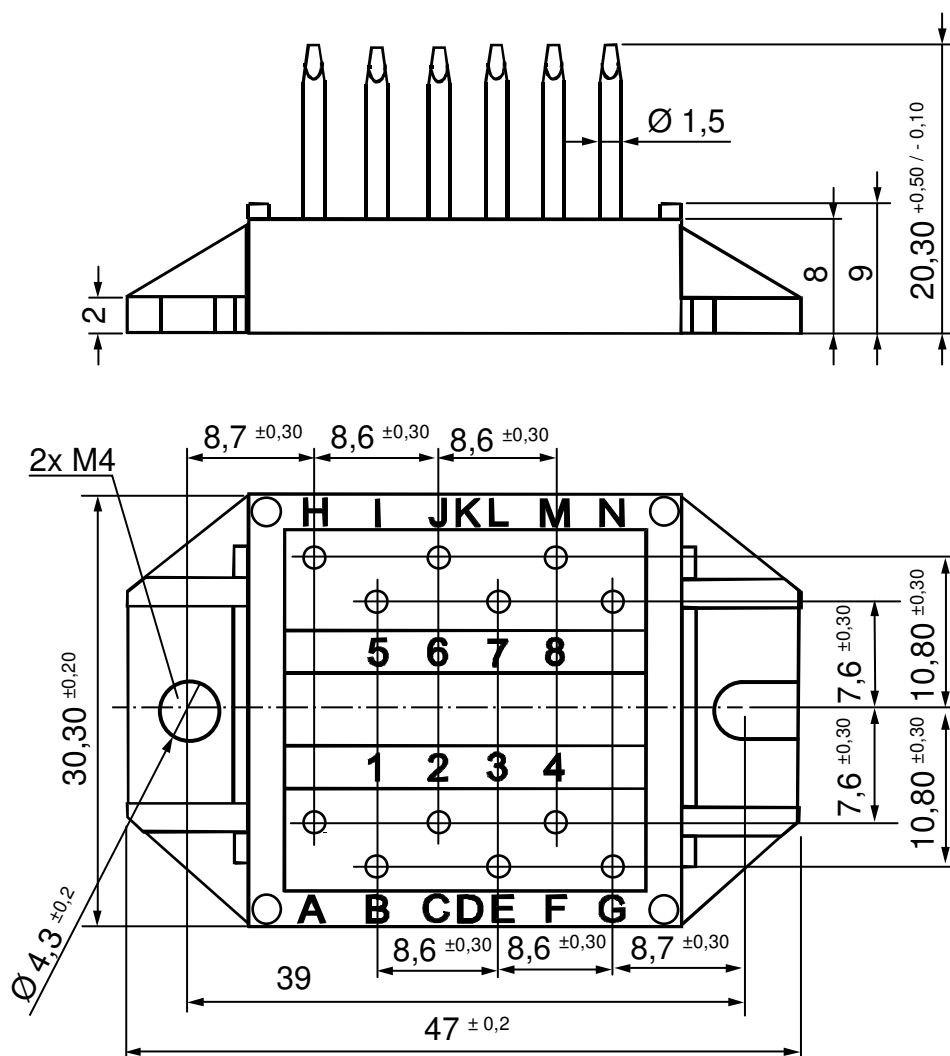
$T_{VJ} = 125^{\circ}\text{C}$



Thyristor

$V_{0 \max}$	<i>threshold voltage</i>	0,88	V
$R_{0 \max}$	<i>slope resistance *</i>	18	mΩ

Outlines ECO-PAC1



Thyristor

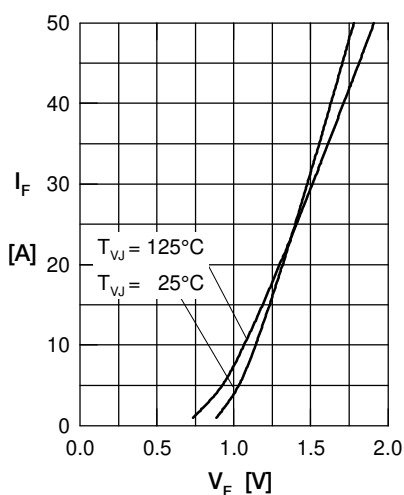


Fig. 1 Forward current vs. voltage drop per thyristor

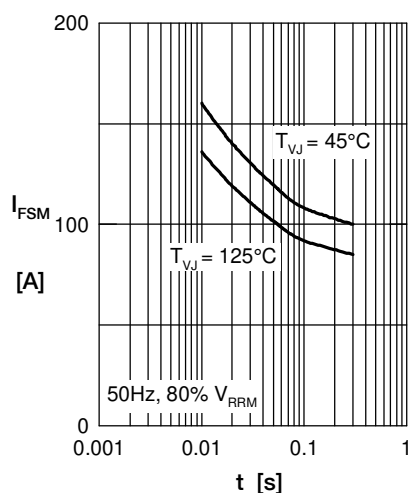


Fig. 2 Surge overload current vs. time per thyristor

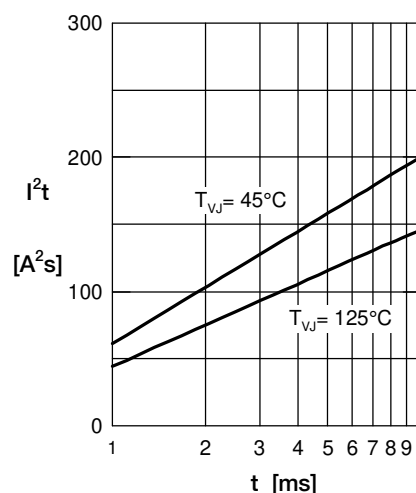


Fig. 3 I^2t vs. time per thyristor

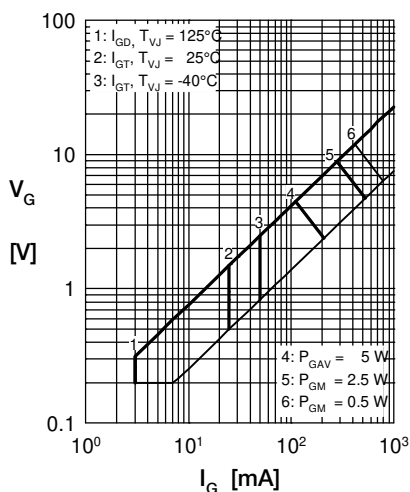


Fig. 4 Gate trigger characteristics

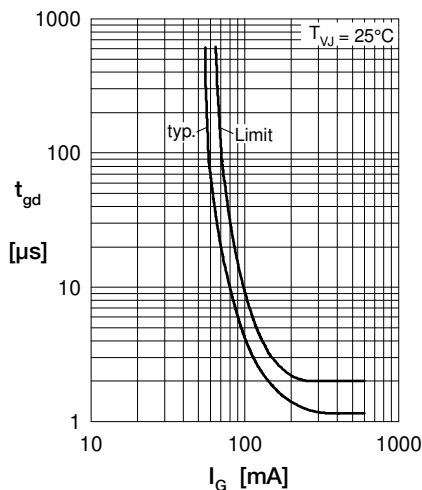


Fig. 5 Gate trigger delay time

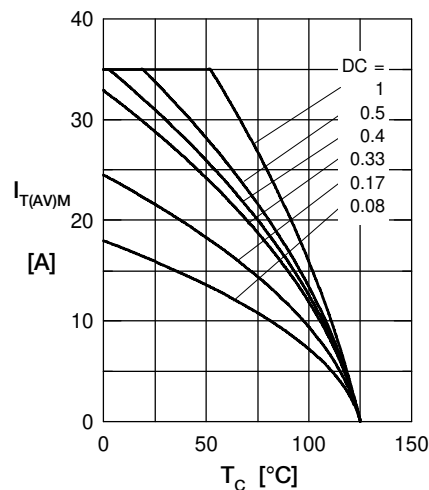


Fig. 5 Max. forward current vs. case temperature per thyristor

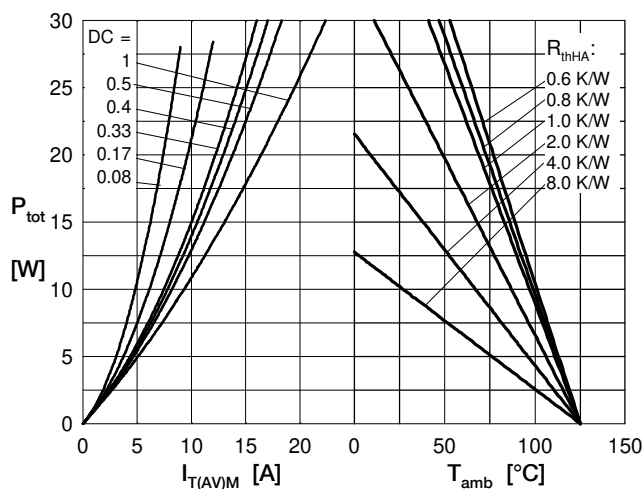


Fig. 4 Power dissipation vs. forward current and ambient temperature per thyristor

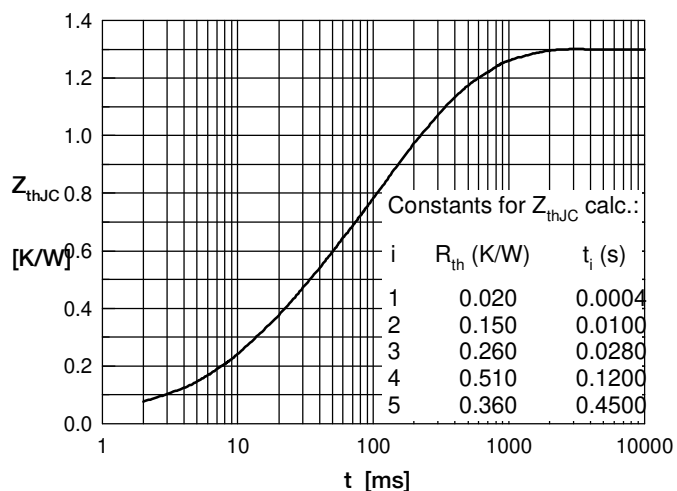


Fig. 6 Transient thermal impedance junction to case vs. time per thyristor